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(54) **SEMICONDUCTOR DEVICE WITH FINE METAL LINES FOR BEOL STRUCTURE AND METHOD OF MANUFACTURING THE SAME**

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(57)

ABSTRACT

Provided is a semiconductor device including a front-end-of-line (FEOL) structure and a back-end-of-line (BEOL) structure connected to the FEOL structure, wherein the FEOL structure includes at least one source/drain region and at least one gate structure, and the BEOL structure includes: a plurality of 1st fine metal lines arranged in a row with a same pitch, each of the plurality of 1st fine metal lines having a same width; and at least one 1st wide metal line formed at a side of the plurality of 1st fine metal lines, the 1st wide metal line having a width greater than the width of the 1st fine metal line, and wherein each of the plurality of 1st fine metal lines includes a material different from a material included in the 1st wide metal line

